

## P-Channel Power MOSFET

-30V, -36A, 15mΩ

### FEATURES

- Low  $R_{DS(on)}$  to minimize conductive Loss
- Low gate charge for fast power switching
- 100% UIS tested
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

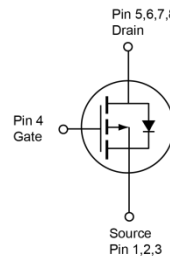
PRODUCT SUMMARY			
PARAMETER	VALUE	UNIT	
$V_{DS}$	-30	V	
$R_{DS(on)}$ (max)	$V_{GS} = -10V$	15	mΩ
	$V_{GS} = -4.5V$	30	
$Q_g$	14.3	nC	

### APPLICATIONS

- DC-DC Converters
- Battery Power Management
- Oring FET/Load Switch



PDFN33



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current (Note 1)	$I_D$	$T_C = 25^\circ\text{C}$	-36
		$T_A = 25^\circ\text{C}$	-10
Pulsed Drain Current (Note 1)	$I_{DM}$	-144	A
Single Pulse Avalanche Current (Note 2)	$I_{AS}$	-31	A
Single Pulse Avalanche Energy (Note 2)	$E_{AS}$	48	mJ
Total Power Dissipation	$P_D$	$T_C = 25^\circ\text{C}$	27.8
		$T_C = 125^\circ\text{C}$	5.5
Total Power Dissipation	$P_D$	$T_A = 25^\circ\text{C}$	2.3
		$T_A = 125^\circ\text{C}$	0.5
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	- 55 to +150	$^\circ\text{C}$

THERMAL RESISTANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Thermal Resistance – Junction to Case	$R_{\theta JC}$	4.5	$^\circ\text{C/W}$
Thermal Resistance – Junction to Ambient	$R_{\theta JA}$	53	$^\circ\text{C/W}$

**Notes:**  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\theta JA}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

<b>ELECTRICAL CHARACTERISTICS</b> ( $T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNIT
<b>Static</b> (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	$BV_{DSS}$	-30	--	--	V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250\mu A$	$V_{GS(TH)}$	-1.2	-1.6	-2.5	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	$I_{GSS}$	--	--	$\pm 100$	nA
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = -30V$	$I_{DSS}$	--	--	-1	$\mu A$
Drain-Source On-State Resistance	$V_{GS} = -10V, I_D = -10A$	$R_{DS(on)}$	--	13	15	m $\Omega$
	$V_{GS} = -4.5V, I_D = -10A$		--	22	30	
Forward Transconductance	$V_{DS} = -5V, I_D = -10A$	$g_{fs}$	--	19	--	S
<b>Dynamic</b> (Note 4)						
Total Gate Charge	$V_{GS} = -10V, V_{DS} = -15V, I_D = -10A$	$Q_g$	--	29.3	--	nC
Total Gate Charge	$V_{GS} = -4.5V, V_{DS} = -15V, I_D = -10A$	$Q_g$	--	14.3	--	
Gate-Source Charge		$Q_{gs}$	--	5.9	--	
Gate-Drain Charge		$Q_{gd}$	--	5.2	--	
Input Capacitance	$V_{GS} = 0V, V_{DS} = -15V, f = 1.0\text{MHz}$	$C_{iss}$	--	1829	--	pF
Output Capacitance		$C_{oss}$	--	227	--	
Reverse Transfer Capacitance		$C_{rss}$	--	160	--	
<b>Switching</b> (Note 4)						
Turn-On Delay Time	$V_{GS} = -10V, V_{DS} = -15V, I_D = -1A, R_G = 6\Omega,$	$t_{d(on)}$	--	9	--	ns
Rise Time		$t_r$	--	21.8	--	
Turn-Off Delay Time		$t_{d(off)}$	--	59.8	--	
Fall Time		$t_f$	--	14.4	--	
<b>Source-Drain Diode</b> (Note 3)						
Diode Forward Voltage	$V_{GS} = 0V, I_S = -10A$	$V_{SD}$	--	--	-1	V
Reverse Recovery Time	$I_S = -10A, di/dt = 100A/\mu s$	$t_{rr}$	--	34	--	ns
Reverse Recovery Charge		$Q_{rr}$	--	23	--	nC

**Notes:**

- Current limited by package.
- $L = 0.1\text{mH}, V_{GS} = -10V, V_{DS} = -25V, R_G = 25\Omega, I_{AS} = -31A$ , Starting  $T_J = 25^\circ\text{C}$
- Pulse test: Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- Switching time is essentially independent of operating temperature.

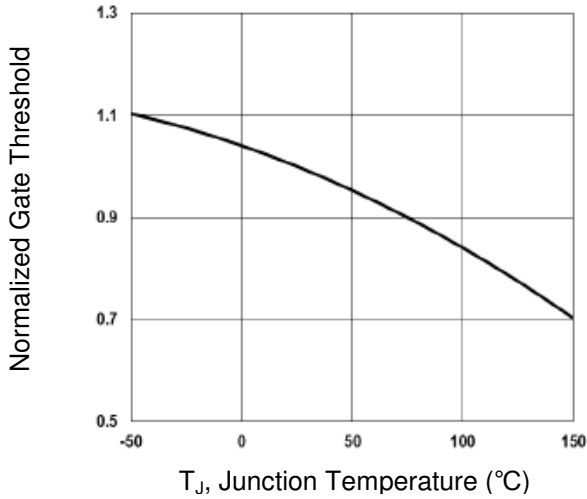
**ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM150P03PQ33 RGG	PDFN33	5,000pcs / 13" Reel

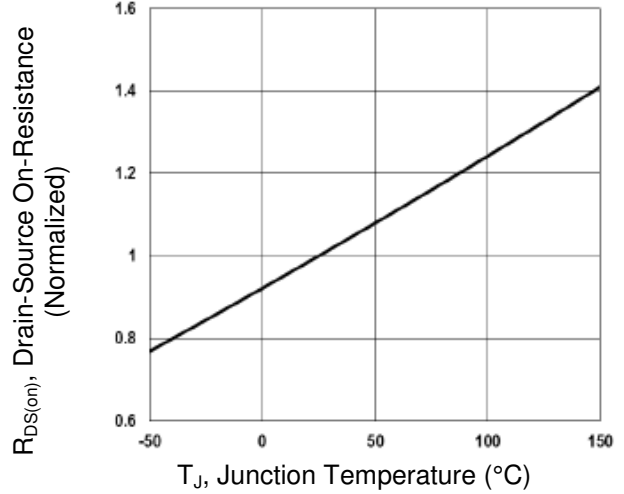
**CHARACTERISTICS CURVES**

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

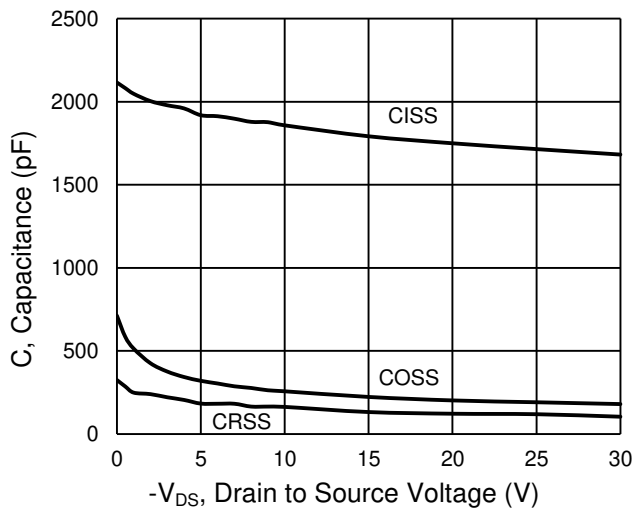
**Normalized  $V_{th}$  vs.  $T_J$**



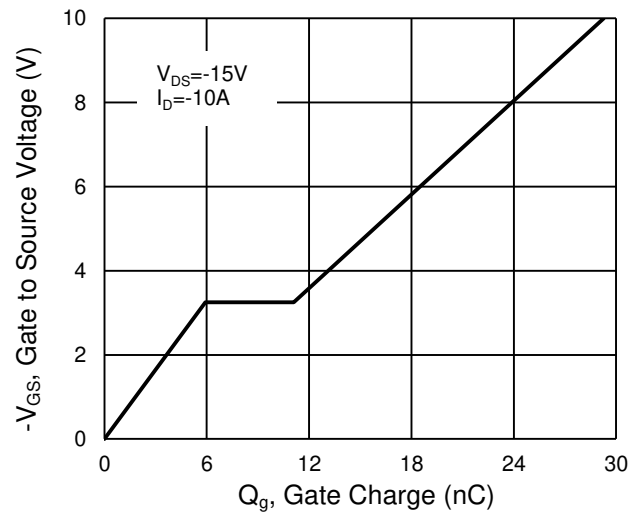
**On-Resistance vs. Junction Temperature**



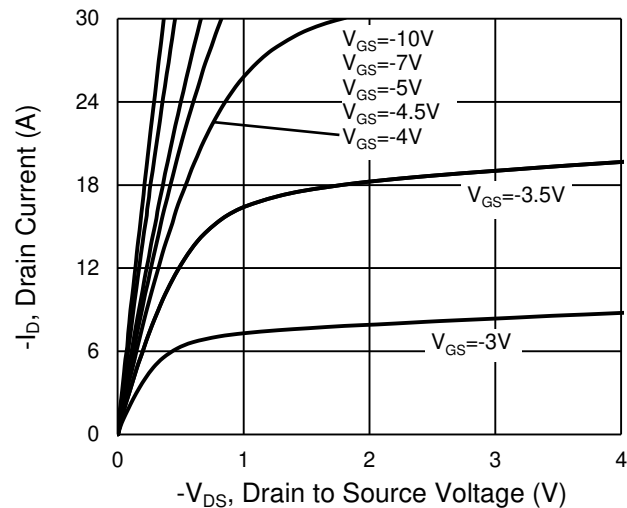
**Capacitance vs. Drain-Source Voltage**



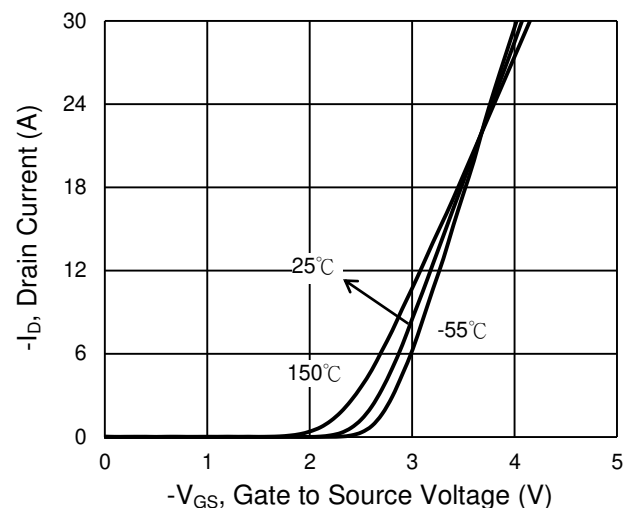
**Gate-Source Voltage vs. Gate Charge**



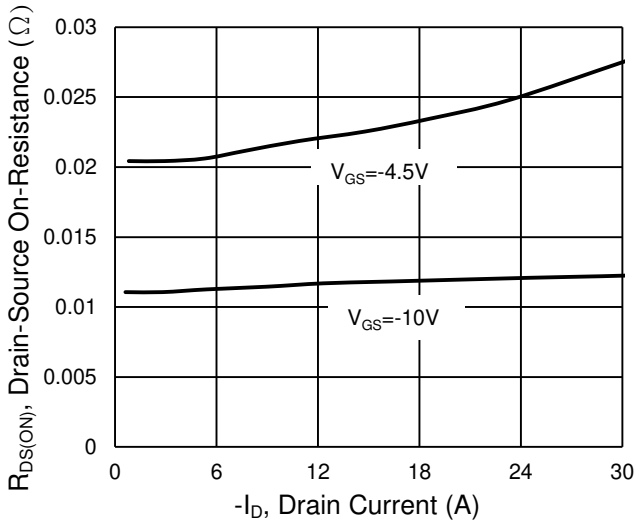
**Output Characteristics**



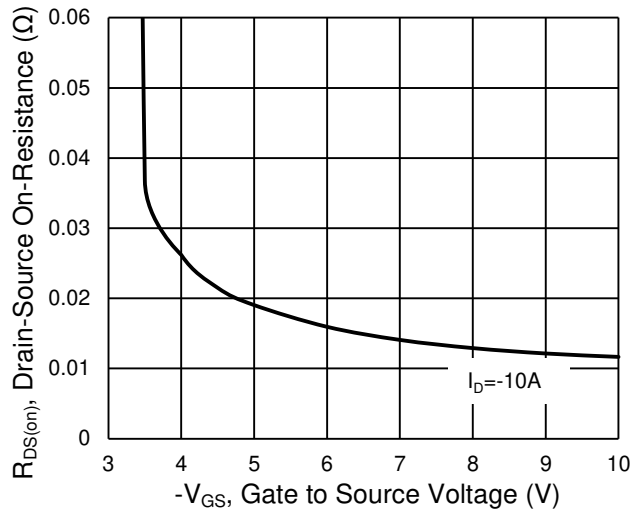
**Transfer Characteristics**



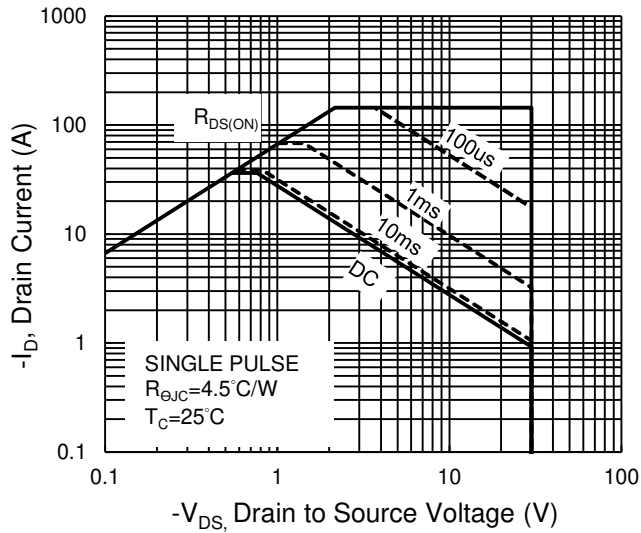
**On-Resistance vs. Drain Current**



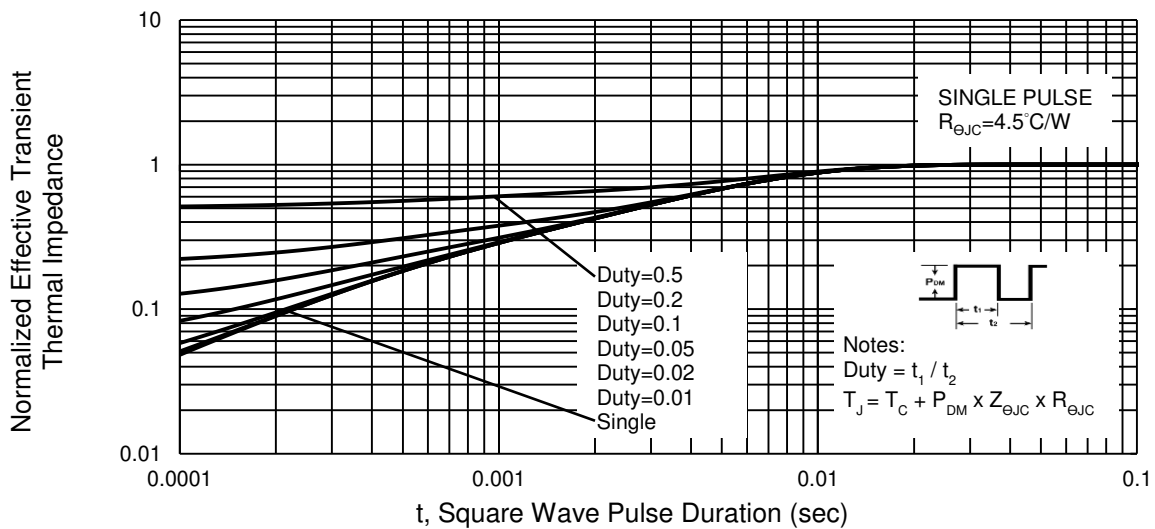
**On-Resistance vs. Gate-Source Voltage**



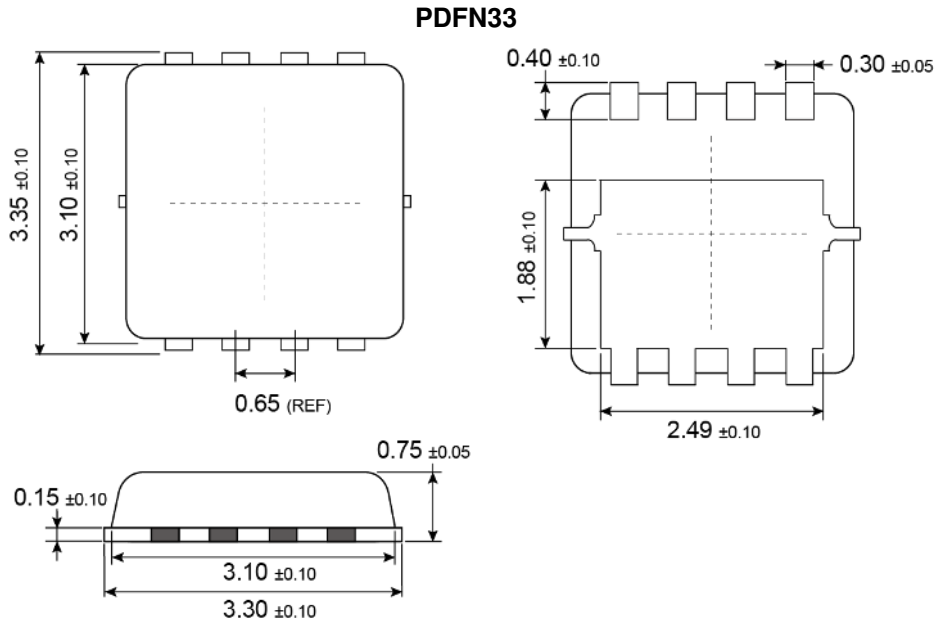
**Maximum Safe Operating Area, Junction-to-Case**



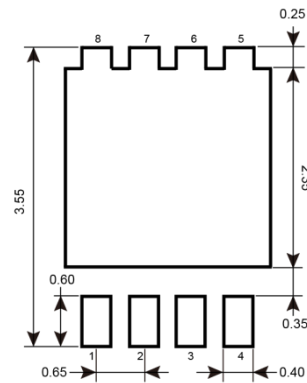
**Normalized Thermal Transient Impedance, Junction-to-Case**



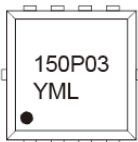
**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)



**SUGGESTED PAD LAYOUT** (Unit: Millimeters)



**MARKING DIAGRAM**



- Y** = Year Code
- M** = Month Code for Halogen Free Product
  - O** =Jan
  - P** =Feb
  - Q** =Mar
  - R** =Apr
  - S** =May
  - T** =Jun
  - U** =Jul
  - V** =Aug
  - W** =Sep
  - X** =Oct
  - Y** =Nov
  - Z** =Dec
- L** = Lot Code (1~9, A~Z)

## Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale. c